

Silicon NPN Power Transistors

2SC1444

DESCRIPTION

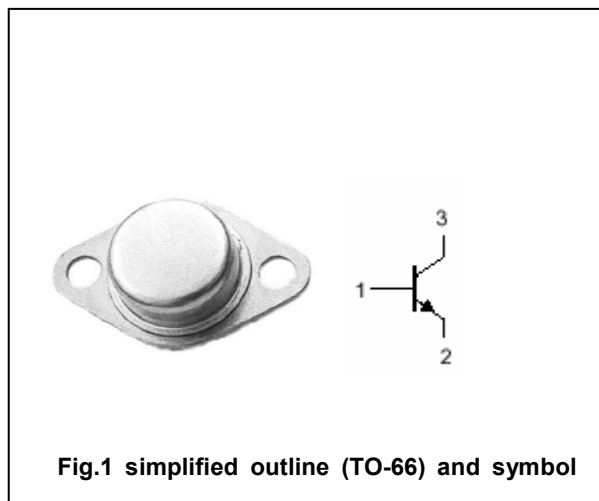
- With TO-66 package
- Excellent safe operating area
- Low collector saturation voltage

APPLICATIONS

- For switching and wide-band amplifier applications.

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	80	V
V_{CEO}	Collector-emitter voltage	Open base	60	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		6	A
I_B	Base current		1	A
P_D	Total power dissipation	$T_C = 25 \square$	40	W
T_j	Junction temperature		150	\square
T_{stg}	Storage temperature		-55~150	\square

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =30mA ; I _B =0	60			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =6A ; I _B =1A			1.5	V
V _{BE}	Base-emitter on voltage	I _C =6A ; V _{CE} =4V			2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =80V ; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =6V ; I _C =0			0.1	mA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =4V	30			
h _{FE-2}	DC current gain	I _C =3A ; V _{CE} =4V	15			
f _T	Transition frequency	I _C =0.5A ; V _{CE} =10V		10		MHz

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PACKAGE OUTLINE

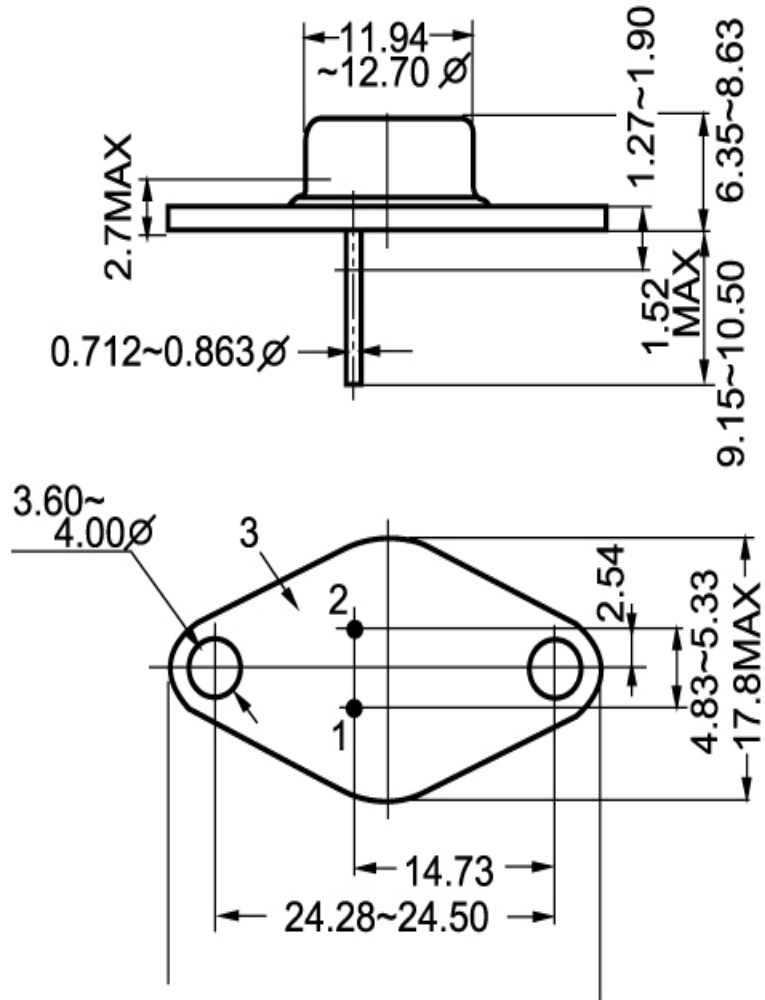


Fig.2 outline dimensions